

LY61L10268A 1024k x 8 bit high speed cmos sram

REVISION HISTORY

<u>Revision</u> Rev. 1.0	Description Initial Issue	<u>Issue Date</u> Jan.21.2014
Rev. 1.1	Corrected IsB1 in DC ELECTRICAL CHARACTERISTICS	Dec.22.2016
	Revised PIN DESCRIPTION in page 1	
	Deleted WRITE CYCLE Notes :	
	1. WE#,CE# must be high during all address transitions. In page 6.	



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FEATURES

- Fast access time : 8/10ns
- Low power consumption:

Operating current: 90/80mA (TYP.) Standby current: 3mA (TYP.)

- Single 3.3V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- Data retention voltage : 1.5V (MIN.)
- Green package available
- Package : 48-ball 6mm x 8mm TFBGA

PRODUCT FAMILY

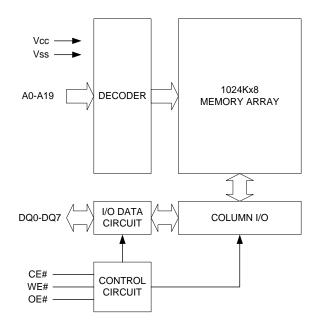
GENERAL DESCRIPTION

The LY61L10268A is a 16M-bit high speed CMOS static random access memory organized as 1,024K words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The LY61L10268A operates from a single power supply of 3.3V and all inputs and outputs are fully TTL compatible.

Product	Operating	Vec Bongo	Speed	issipation	
Family	Temperature	V _{CC} Range	Speed	Standby(I _{SB1} ,TYP.)	Operating(I _{CC} ,TYP.)
LY61L10268A	0 ~ 70°C	3.0 ~ 3.6V	8/10ns	3mA	90/80mA
LY61L10268A(I)	-40 ~ 85℃	3.0 ~ 3.6V	8/10ns	3mA	90/80mA
LY61L10268A	0 ~ 70°C	2.7 ~ 3.6V	10ns	3mA	80mA
LY61L10268A(I)	-40 ~ 85° ℃	2.7 ~ 3.6V	10ns	3mA	80mA

FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

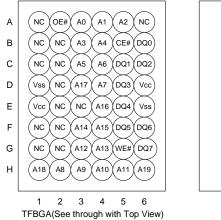
SYMBOL	DESCRIPTION
A0 - A19	Address Inputs
DQ0 - DQ7	Data Inputs/Outputs
CE#	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
Vcc	Power Supply
Vss	Ground
NC	No Connection

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PIN CONFIGURATION





ABSOLUTE MAXIMUN RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on Vcc relative to Vss	V _{T1} -0.5 to 4.6		V
Voltage on any other pin relative to Vss	V _{T2}	-0.5 to Vcc+0.5	V
	т.	0 to 70(C grade)	°C
Operating Temperature	Та	-40 to 85(I grade)	C
Storage Temperature	T _{STG}	-65 to 150	°C
Power Dissipation	PD	1	W
DC Output Current	Іоит	50	mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	Н	Х	Х	High-Z	I _{SB1}
Output Disable	L	Н	Н	High-Z	lcc
Read	L	L	Н	Dout	lcc
Write	L	Х	L	D _{IN}	lcc

Note: $H = V_{IH}$, $L = V_{IL}$, X = Don't care.



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DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP. *4	MAX.	UNIT
Supply Voltage	Vcc		-8	3.0	3.3	3.6	V
Supply vollage	VCC		-10	2.7	3.3	3.6	V
Input High Voltage	VIH ^{*1}			2.2	-	Vcc+0.3	V
Input Low Voltage	V1L*2			- 0.3	-	0.8	V
Input Leakage Current	ILI	$V_{CC} \ge V_{IN} \ge V_{SS}$		- 1	-	1	μA
Output Leakage Current	Ilo	Vcc≧ Vou⊤≧ Vss, Output Disabled		- 1	-	1	μA
Output High Voltage	Vон	Iон = -4mA		2.4	-	-	V
Output Low Voltage	Vol	lo∟ = 8mA		-	-	0.4	V
Average Operating	lcc	CE# ≤ 0.2 , Others at 0.2V or V _{CC} -0.2V	-8	-	90	120	mA
Power Supply Current		$I_{1/0} = 0$ mA; f=max		-	80	110	mA
Standby Power Supply Current	I _{SB1}	$\begin{array}{lll} CE\# \geqq & V_{CC} \text{ - } 0.2V, \\ Others at 0.2V \text{ or } V_{CC} \text{ - } 0.2V \end{array}$		-	3	40	mA

Notes:

1. $V_{IH}(max) = V_{CC} + 2.0V$ for pulse width less than 6ns.

2. $V_{IL}(min) = V_{SS} - 2.0V$ for pulse width less than 6ns.

3. Over/Undershoot specifications are characterized on engineering evaluation stage, not for mass production test.

4. Typical values are included for reference only and are not guaranteed or tested.

Typical valued are measured at V_CC = V_CC(TYP.) and T_{A} = 25 $^\circ\text{C}$

<u>CAPACITANCE</u> (T_A = 25°C, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	Cin	-	8	pF
Input/Output Capacitance	Cı/o	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Speed	10ns
Input Pulse Levels	0.2V to V _{CC} - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	Vcc/2
Output Load	$C_L = 30pF + 1TTL, I_{OH}/I_{OL} = -4mA/8mA$



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AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

PARAMETER	SYM.	LY61L10268A-8		LY61L10268A-10		UNIT
FARAIVIETER	5 T WI.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t _{RC}	8	-	10	-	ns
Address Access Time	t aa	-	8	-	10	ns
Chip Enable Access Time	t ACE	-	8	-	10	ns
Output Enable Access Time	toe	-	4.5	-	4.5	ns
Chip Enable to Output in Low-Z	tcLz*	2	-	2	-	ns
Output Enable to Output in Low-Z	tolz*	0	-	0	-	ns
Chip Disable to Output in High-Z	tснz*	-	3	-	4	ns
Output Disable to Output in High-Z	tонz*	-	3	-	4	ns
Output Hold from Address Change	tон	2	-	2	-	ns

(2) WRITE CYCLE

PARAMETER	SYM.	LY61L10268A-8		LY61L10268A-10		UNIT
FARAIVIETER	5111.	MIN.	MAX.	MIN.	MAX.	UNIT
Write Cycle Time	twc	8	-	10	-	ns
Address Valid to End of Write	taw	6.5	-	8	-	ns
Chip Enable to End of Write	tcw	6.5	-	8	-	ns
Address Set-up Time	t _{AS}	0	-	0	-	ns
Write Pulse Width	twp	6.5	-	8	-	ns
Write Recovery Time	twR	0	-	0	-	ns
Data to Write Time Overlap	tow	5	-	6	-	ns
Data Hold from End of Write Time	t _{DH}	0	-	0	-	ns
Output Active from End of Write	tow*	2	-	2	-	ns
Write to Output in High-Z	twHz*	-	3	-	4	ns

*These parameters are guaranteed by device characterization, but not production tested.

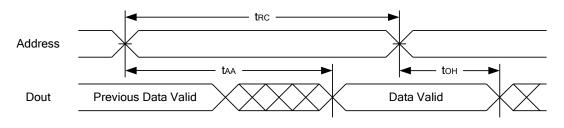


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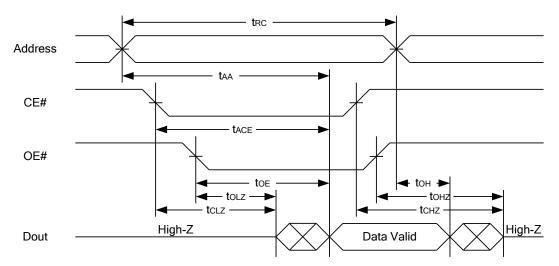
Rev. 1.1

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)



Notes :

1.WE# is high for read cycle.

2.Device is continuously selected OE# = low, CE# = low.

3.Address must be valid prior to or coincident with CE# = low,; otherwise tAA is the limiting parameter.

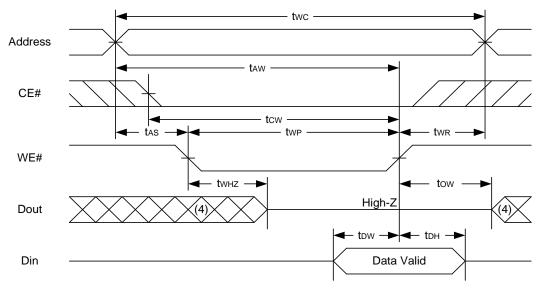
4.t_{CLZ}, t_{OLZ}, t_{CHZ} and t_{OHZ} are specified with C_L = 5pF. Transition is measured ±500mV from steady state.

5.At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ}

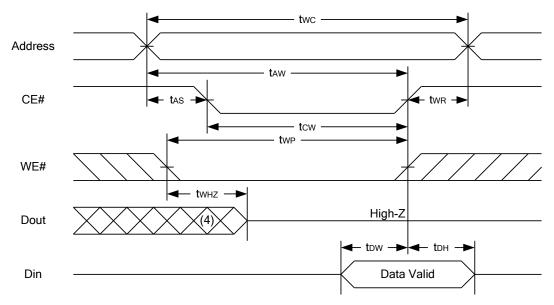


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WRITE CYCLE 1 (WE# Controlled) (1,2,4,5)



WRITE CYCLE 2 (CE# Controlled) (1,4,5)



Notes :

 A write occurs during the overlap of a low CE#, low WE#.
During a WE# controlled write cycle with OE# low, twp must be greater than twHz + tpw to allow the drivers to turn off and data to be placed on the bus.

- 3. During this period, I/O pins are in the output state, and input signals must not be applied.
- 4.If the CE# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
- 5.tow and twHz are specified with $C_L = 5pF$. Transition is measured ±500mV from steady state.



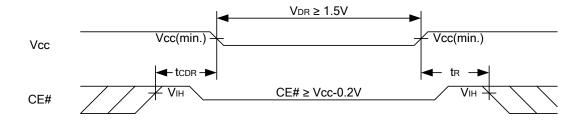
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DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	Vdr	$CE# \ge V_{CC} - 0.2V$	1.5	-	3.6	V
Data Retention Current		$V_{CC} = 1.5V, CE\# \ge V_{CC} - 0.2V$ Others at 0.2V or $V_{CC} - 0.2V$	-	3	25	mA
Chip Disable to Data Retention Time	tcdr	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC*}	-	-	ns

tRC* = Read Cycle Time

DATA RETENTION WAVEFORM

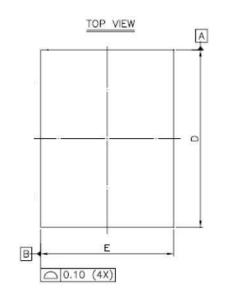


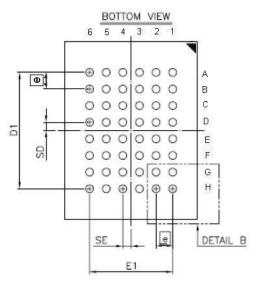


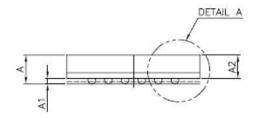
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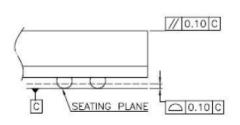
PACKAGE OUTLINE DIMENSION

48-ball 6mm × 8mm TFBGA Package Outline Dimension





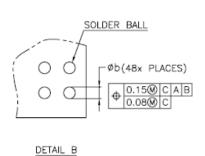




SIDE VIEW



CVL	D	IMENSIO (mm)	N	DIMENSION (inch)			
SYM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А		—	1.40		_	0.055	
A1	0.20	0.25	0.30	0.008	0.010	0.012	
A2		1.05				0.041	
b	0.30	0.35	0.40	0.012	0.014	0.016	
D	7.95	8.00	8.05	0.313	0.315	0.317	
D1	5	.25 BSC	2	0.207 BSC			
E	5.95	6.00	6.05	0.234	0.236	0.238	
E1	3	.75 BSC		0	148 BS	SC	
SE	0.375 TYP			0.015 TYP			
SD	0.375 TYP			0.015 TYP			
e	0	.75 BSC)	0.030 BSC			



NOTE:

1. CONTROLLING DIMENSION : MILLIMETER.

2. REFERENCE DOCUMENT : JEDEC MO-207.

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ORDERING INFORMATION

Package Type	Access Time (Speed/ns)	Temperature Range(℃)	Packing Type	Lyontek Item No.
48-ball (6mm x 8mm) TFBGA	8	0℃~70℃	Tray	LY61L10268AGL-8
			Tape Reel	LY61L10268AGL-8T
		-40℃~85℃	Tray	LY61L10268AGL-8I
			Tape Reel	LY61L10268AGL-8IT
	10	0°C ~70°C	Tray	LY61L10268AGL-10
			Tape Reel	LY61L10268AGL-10T
		-40℃~85℃	Tray	LY61L10268AGL-10I
			Tape Reel	LY61L10268AGL-10IT



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